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**UPDATE CHANGE NOTIFICATION # 20075**Generic Copy

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**Issue Date:** 03-Sep-2013

**TITLE:** Update Change Notification to FPCN20075 for wafer fab transfer from Gunma in Japan to Niigata in Japan (2SK596S-B and 2SK596S-C).

**PROPOSED FIRST SHIP DATE:** 03-Dec-2013 (or earlier with customer approval)  
<The actual ship date will be different by each product, please check the responsible Sales Person.>

**AFFECTED CHANGE CATEGORY(S):** Wafer Fabrication Location Change

**SAMPLES:** Contact your local ON Semiconductor Sales Office

**FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:**  
Contact your local ON Semiconductor Sales Office or Kazunori Akita  
<[Kazunori.Akita@onsemi.com](mailto:Kazunori.Akita@onsemi.com)>

**ADDITIONAL RELIABILITY DATA:** Available  
Contact your local ON Semiconductor Sales Office or Kazutoshi Kitazume  
<[Kazutoshi.Kitazume@onsemi.com](mailto:Kazutoshi.Kitazume@onsemi.com)>

**NOTIFICATION TYPE:**  
Update Change Notification to FPCN

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <[quality@onsemi.com](mailto:quality@onsemi.com)>.

**DESCRIPTION AND PURPOSE:**

FPCN20075 announced Die change for 2SK596S-B and 2SK596S-C on 26-Apr-2013.

This is an update notification to announce the transfer of products (2SK596S-B and 2SK596S-C) from Sanyo wafer fabrication site located in Gunma to Niigata.

After FPCN20075 announced, the product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed for each product to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.

**UPDATE CHANGE NOTIFICATION #20075****RELIABILITY DATA SUMMARY:**

Test:	Conditions:	Interval:	Results
High Temperature Reverse Bias	Ta=150degC, VGDO=20V	1000 hrs	Pass
Temp Humidity Storage	Ta=85degC, RH=85%	1000 hrs	Pass
Temperature Cycle	Ta=-55degC to 150degC 30min each	100 cycles	Pass
Pressure Cooker	Ta=121degC, $2.03 \times 10^5$ Pa, 100%	50 hrs	Pass
High Temperature Storage	Ta=150degC	1000 hrs	Pass
Low Temperature Storage	Ta=-55degC	1000 hrs	Pass
Solder Test	Ta=260degC $\pm$ 5degC,	10 s	Pass

Notice) ※1 Pre-treatment: Resistance to Soldering heat (Flow:260degC/10s)

**ELECTRICAL CHARACTERISTIC SUMMARY:**

There is no change in electrical parametric performance. Characterization data is available upon request.

**CHANGED PART IDENTIFICATION:**

No change to current part marking will occur. Marking traceability codes will be able to identify wafer fab die source.

**List of affected parts:**

2SK596S-B  
2SK596S-C